

NVTFS4C25N

Power MOSFET

30 V, 17 mΩ, 22 A, Single N-Channel, μ8FL

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- NVTFS4C25NWF – Wettable Flanks Product
- NVT Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	30	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 5)	Steady State	$T_A = 25^\circ\text{C}$	I_D 10.1	A
		$T_A = 85^\circ\text{C}$	7.8	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3, 5)		$T_A = 25^\circ\text{C}$	P_D 3.0	W
		$T_A = 85^\circ\text{C}$	1.8	
Continuous Drain Current $R_{\psi JC}$ (Notes 1, 2, 4, 5)	Steady State	$T_C = 25^\circ\text{C}$	I_D 22.1	A
		$T_C = 85^\circ\text{C}$	17.1	
Power Dissipation $R_{\psi JC}$ (Notes 1, 2, 4, 5)		$T_C = 25^\circ\text{C}$	P_D 14.3	W
		$T_C = 85^\circ\text{C}$	8.6	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM} 90	A	
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	14	A	
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}, I_L = 6.7 A_{pk}, L = 0.5 \text{ mH}$)	E_{AS}	11.2	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The entire application environment impacts the thermal resistance values shown; they are not constants and are valid for the specific conditions noted.
2. Psi (ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to a single case surface.
3. Surface-mounted on FR4 board using 650 mm², 2 oz. Cu Pad.
4. Assumes heat-sink sufficiently large to maintain constant case temperature independent of device power.
5. Continuous DC current rating. Maximum current for pulses as long as one second is higher but dependent on pulse duration and duty cycle.

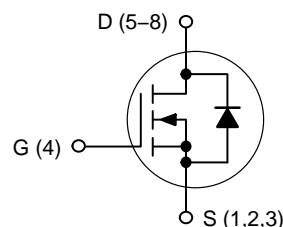


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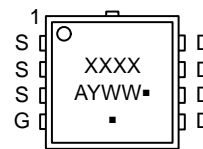
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	17 mΩ @ 10 V	22 A
	26.5 mΩ @ 4.5 V	

N-Channel MOSFET



WDFN8
(μ8FL)
CASE 511AB

MARKING DIAGRAM



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain) (Notes 6, 7 and 9)	$\Psi_{\theta JC}$	10.5	°C/W
Junction-to-Ambient – Steady State (Notes 6 and 8)	$R_{\theta JA}$	50	

6. The entire application environment impacts the thermal resistance values shown; they are not constants and are valid for the specific conditions noted.
7. Psi (ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to a single case surface.
8. Surface-mounted on FR4 board using 650 mm², 2 oz. Cu Pad.
9. Assumes heat-sink sufficiently large to maintain constant case temperature independent of device power.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			15.3		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$			1.0	μA
		$T_J = 125^\circ\text{C}$			10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 10)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.3		2.2	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-4.5		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 9\text{ A}$		13	17	m Ω
				21	26.5	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$		23		S
Gate Resistance	R_G	$T_A = 25^\circ\text{C}$		1.0		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		500		pF
Output Capacitance	C_{OSS}			295		
Reverse Transfer Capacitance	C_{RSS}			85		
Capacitance Ratio	C_{RSS}/C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 15\text{ V}, f = 1\text{ MHz}$		0.170		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 20\text{ A}$		5.1		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.9		
Gate-to-Source Charge	Q_{GS}			1.7		
Gate-to-Drain Charge	Q_{GD}			2.7		
Gate Plateau Voltage	V_{GP}			3.3		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 20\text{ A}$		10.3		nC

SWITCHING CHARACTERISTICS (Note 11)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 10\text{ A}, R_G = 3.0\ \Omega$		8.0		ns
Rise Time	t_r			32		
Turn-Off Delay Time	$t_{d(OFF)}$			10		
Fall Time	t_f			3.0		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		4.0		ns
Rise Time	t_r			25		
Turn-Off Delay Time	$t_{d(OFF)}$			13		
Fall Time	t_f			2.0		

10. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
11. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
DRAIN-SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.87	1.2	V
			T _J = 125°C		0.75		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A		18.2		ns	
Charge Time	t _a			9.8			
Discharge Time	t _b			8.4			
Reverse Recovery Charge	Q _{RR}			5.7			nC

10. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

11. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

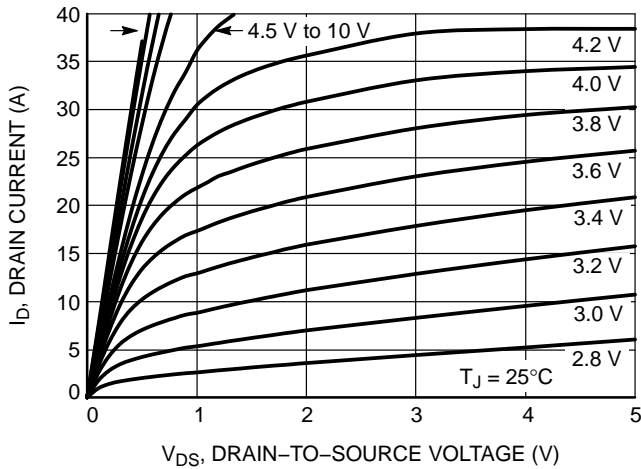


Figure 1. On-Region Characteristics

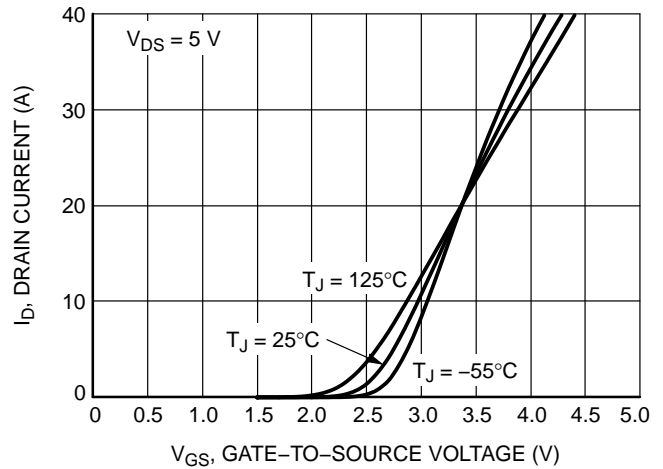


Figure 2. Transfer Characteristics

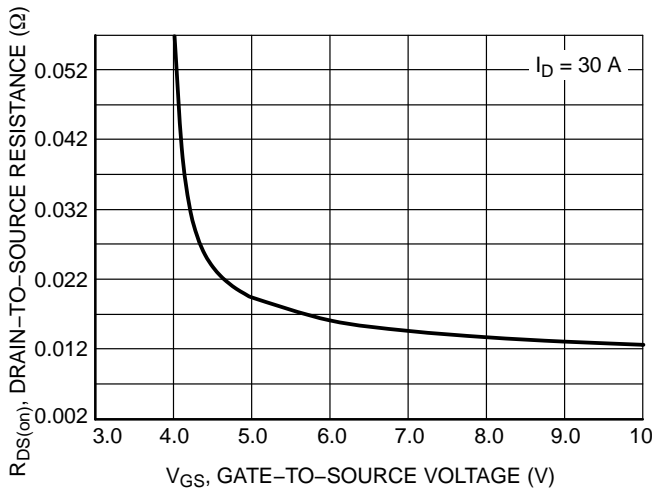


Figure 3. On-Resistance vs. V_{GS}

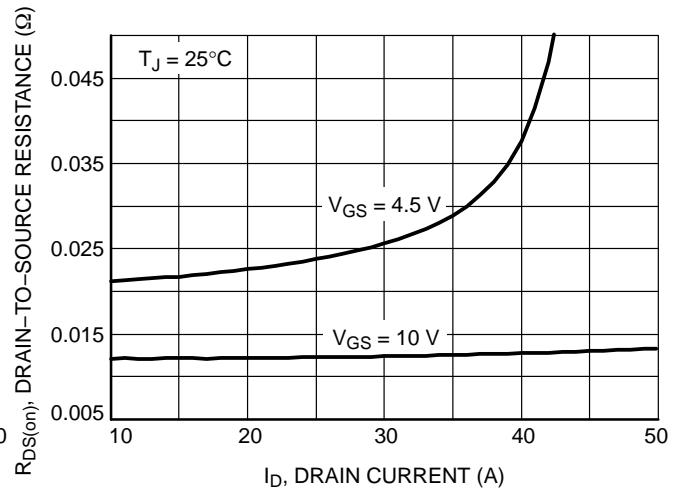


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

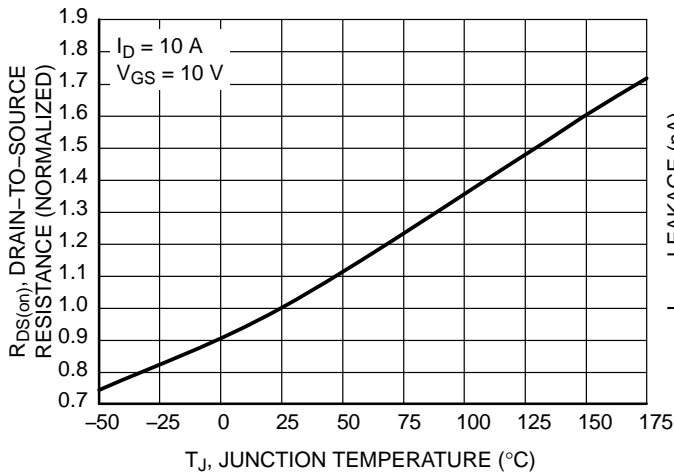


Figure 5. On-Resistance Variation with Temperature

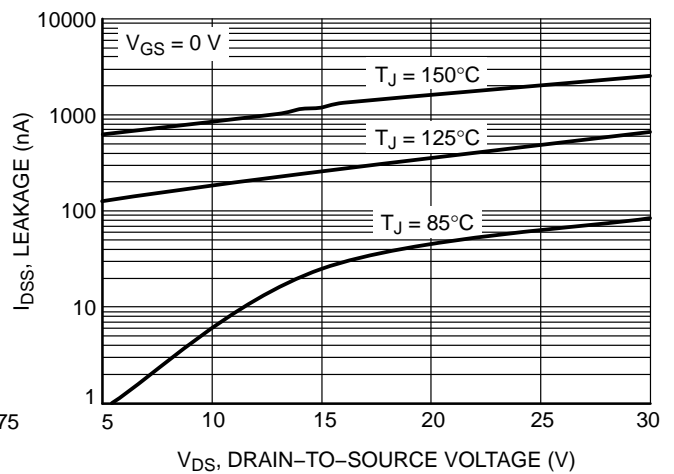


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

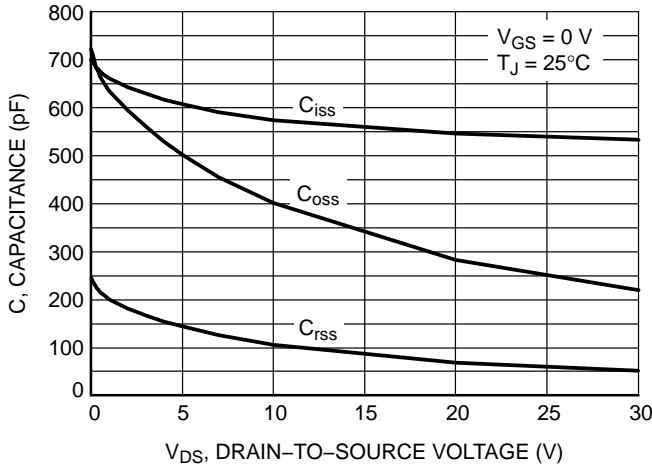


Figure 7. Capacitance Variation

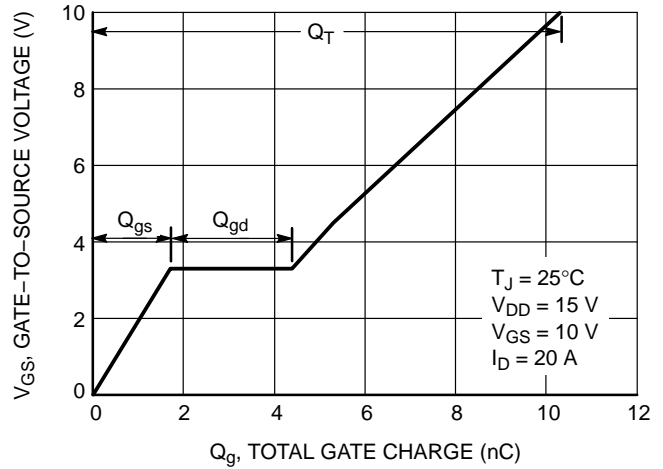


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

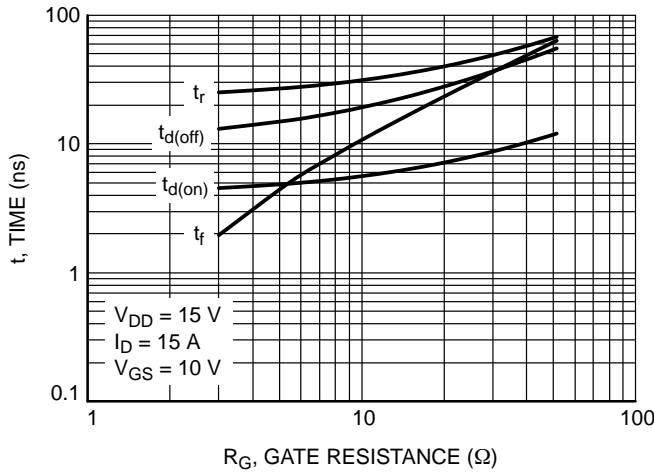


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

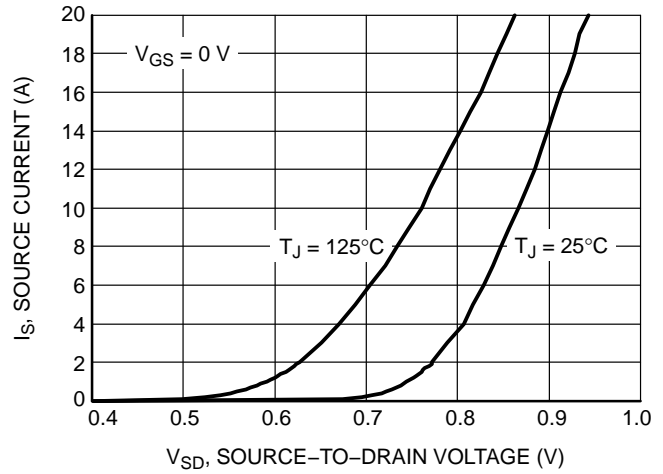


Figure 10. Diode Forward Voltage vs. Current

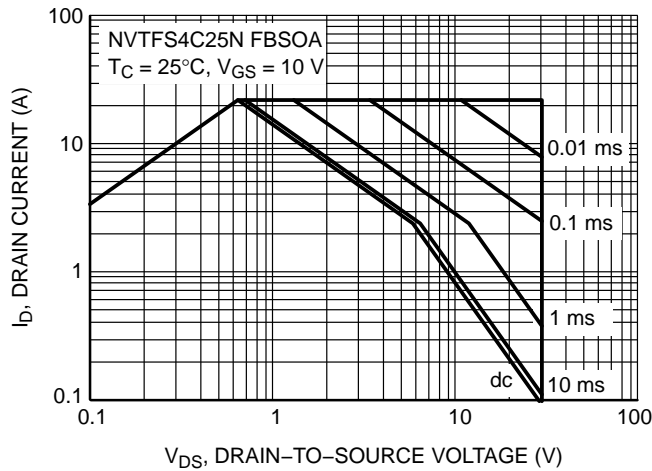


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS

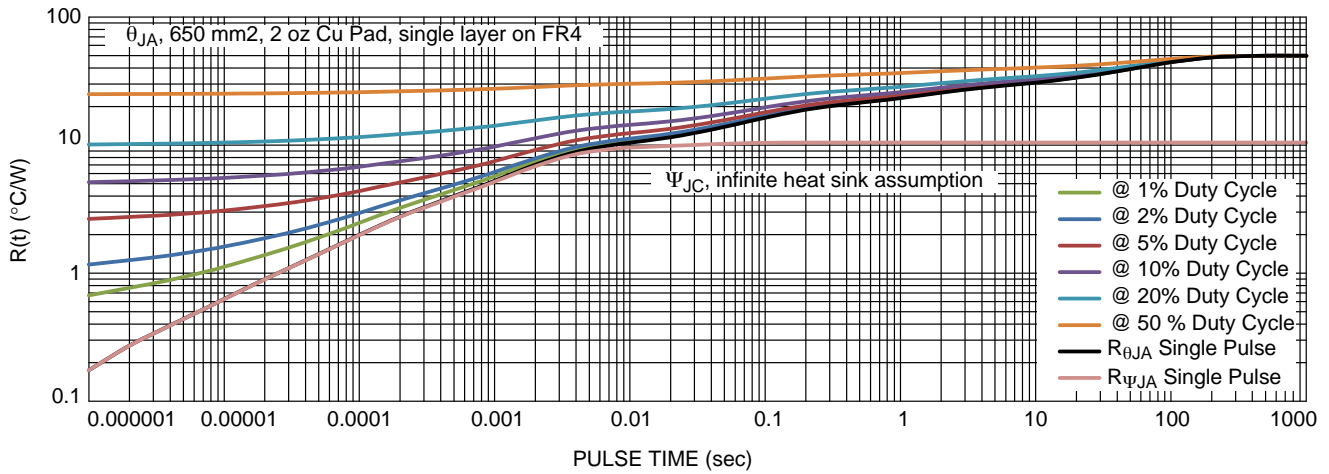


Figure 12. Thermal Response

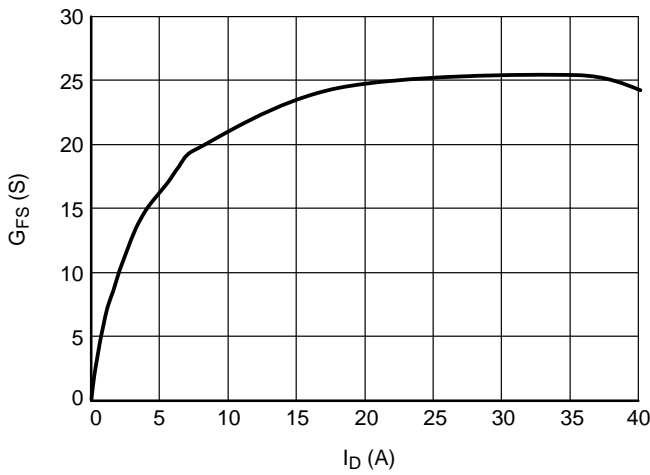


Figure 13. G_{FS} vs. I_D

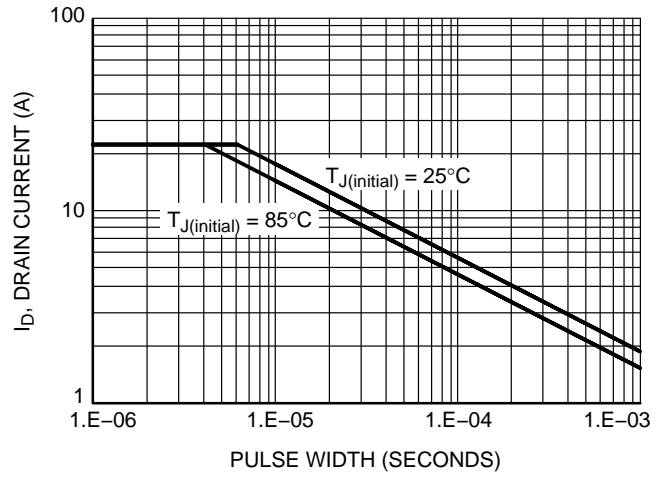


Figure 14. Avalanche Characteristics

ORDERING INFORMATION

Device	Marking	Package	Shipping†
NVTFS4C25NTAG	4V25	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS4C25NWFTAG	25WF	WDFN8 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

